Ordering number:ENN1856A

PNP Epitaxial Planar Silicon Transistor

2SA1435

High h_{FE}, AF Amplifier Applications

Applications

· Low frequency general-purpose amplifiers, drivers, muting circuits.

Features

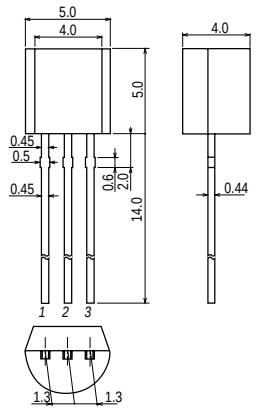
· Adoption of MBIT process.
· High DC current gain (h_{FE}=500 to 1200).
· Large current capacity.
· Low colletor-to-emitter saturation voltage ($V_{CE(sat)}$≤0.5V max).
· High V_{EBO} (V_{EBO}≥15V).

Package Dimensions

unit:mm

2003B

[2SA1435]



1 : Emitter
2 : Collector
3 : Base
SANYO : NP

Specifications

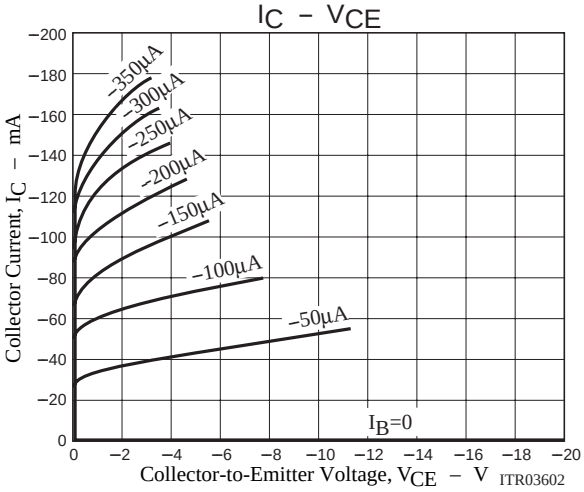
Absolute Maximum Ratings at Ta = 25˚C

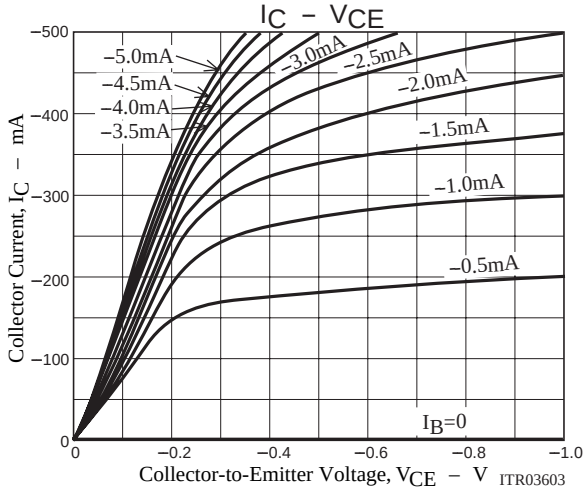
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		–30	V
Collector-to-Emitter Voltage	V_{CEO}		–25	V
Emitter-to-Base Voltage	V_{EBO}		–15	V
Collector Current	I_C		–300	mA
Collector Current (Pulse)	I_{CP}		–500	mA
Collector Dissipation	P_C		600	mW
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

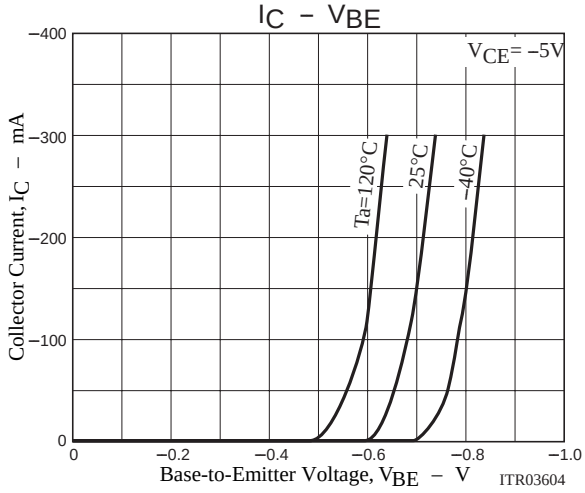
Electrical Characteristics at Ta = 25˚C

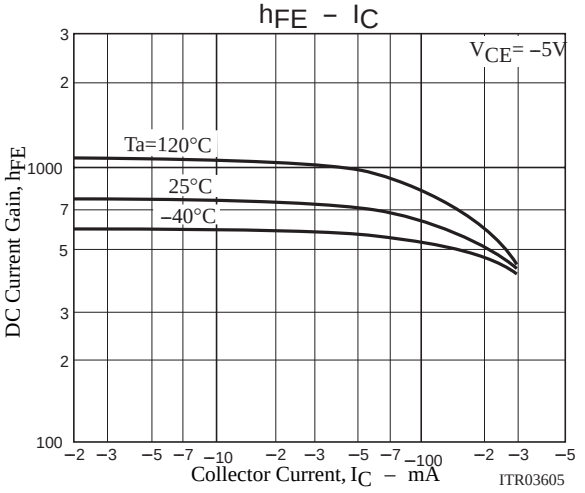
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=–40V, I_E=0			–0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–10V, I_C=0			–0.1	μA
DC Current Gain	$h_{FE}1$	V_{CE}=–5V, I_C=–10mA	500	800	1200	
	$h_{FE}2$	V_{CE}=–5V, I_C=–200mA	200			
Gain-Bandwidth Product	f_T	V_{CE}=–10V, I_C=–10mA		100		MHz
Output Capacitance	C_{ob}	V_{CB}=–10V, f=1MHz		7.5		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=–100mA, I_B=–4mA		–0.2	–0.5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=–100mA, I_B=–4mA		–0.75	–1.1	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10μA, I_E=0	–60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–50			V
Emitter-to-Base Breakdown Votage	$V_{(BR)EBO}$	I_E=–10μA, I_C=0	–15			V

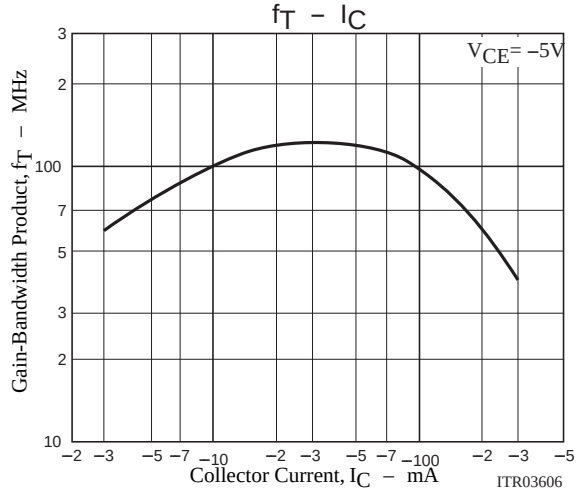
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

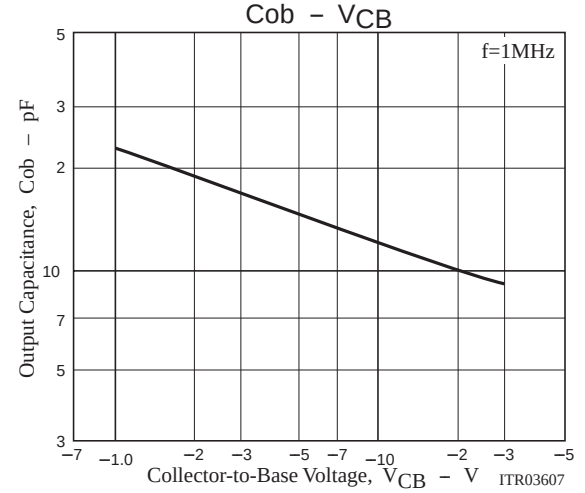

IC – VCE
Collector Current, IC – mA
Collector-to-Emitter Voltage, VCE – V
ITR03602
–350µA
–300µA
–250µA
–200µA
–150µA
–100µA
–50µA
IB=0

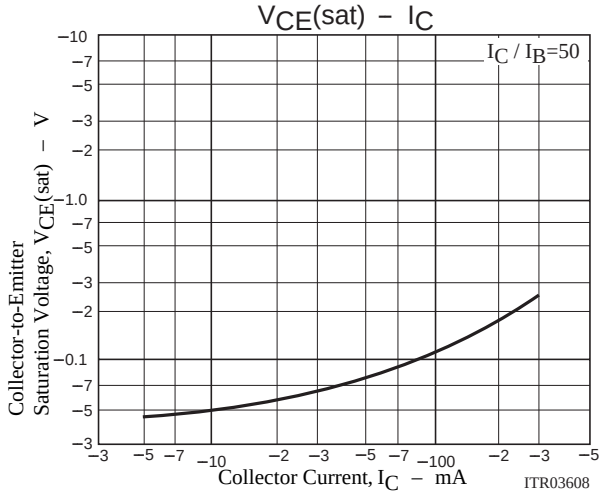

IC – VCE
Collector Current, IC – mA
Collector-to-Emitter Voltage, VCE – V
ITR03603
–5.0mA
–4.5mA
–4.0mA
–3.5mA
–3.0mA
–2.5mA
–2.0mA
–1.5mA
–1.0mA
–0.5mA
IB=0

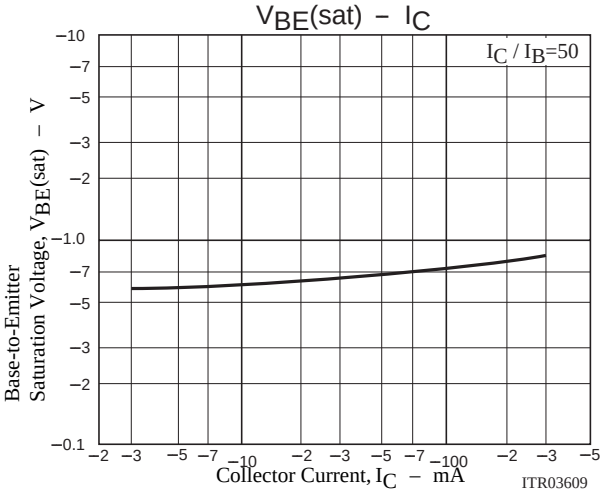

IC – VBE
Collector Current, IC – mA
Base-to-Emitter Voltage, VBE – V
ITR03604
VCE= –5V
Ta=120°C
25°C
–40°C


hFE – IC
DC Current Gain, hFE
Collector Current, IC – mA
ITR03605
VCE= –5V
Ta=120°C
25°C
–40°C

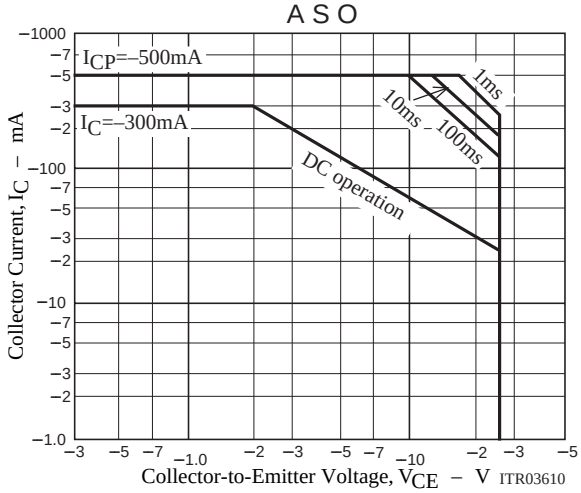

fT – IC
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – mA
ITR03606
VCE= –5V


Cob – VCB
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
ITR03607
f=1MHz


VCE(sat) – IC
Collector-to-Emitter
Saturation Voltage, VCE(sat) – V
Collector Current, IC – mA
ITR03608
IC / IB=50


VBE(sat) – IC
Base-to-Emitter
Saturation Voltage, VBE(sat) – V
Collector Current, IC – mA
ITR03609
IC / IB=50

A S O



PC – Ta